

January 2007

# FOD3180 2A Output Current, High Speed MOSFET Gate Driver Optocoupler

## **Features**

- Guaranteed operating temperature range of -40°C to +100°C
- 2A minimum peak output current
- High speed response: 200ns max propagation delay over temperature range
- 250kHz maximum switching speed
- 30ns typ pulse width distortion
- Wide V<sub>CC</sub> operating range: 10V to 20V
- 5000Vrms, 1 minute isolation
- Under voltage lockout protection (UVLO) with hysteresis
- Minimum creepage distance of 7.0mm
- Minimum clearance distance of 7.0mm
- C-UL, UL and VDE\* safety agency approvals pending
- $\blacksquare$  R<sub>DS(ON)</sub> of 1.5 $\Omega$  (typ.) offers lower power dissipation
- 10kV/µs minimum common mode rejection

## **Applications**

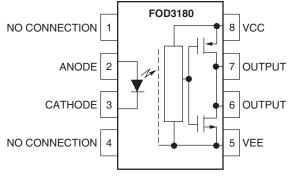
- Plasma Display Panel
- High performance DC/DC convertor
- High performance switch mode power supply
- High performance uninterruptible power supply
- Isolated Power MOSFET gate drive

## **Description**

The FOD3180 is a 2A Output Current, High Speed MOSFET Gate Drive Optocoupler. It consists of a aluminium gallium arsenide (AlGaAs) light emitting diode optically coupled to a CMOS detector with PMOS and NMOS output power transistors integrated circuit power stage. It is ideally suited for high frequency driving of power MOSFETs used in Plasma Display Panels (PDPs), motor control inverter applications and high performance DC/DC converters.

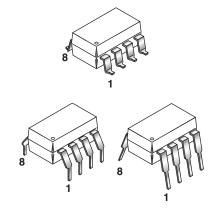
The device is packaged in an 8-pin dual in-line housing compatible with 260°C reflow processes for lead free solder compliance.

# **Functional Block Diagram**



#### Note:

A 0.1µF bypass capacitor must be connected between pins 5 and 8.



<sup>\*</sup>Requires 'V' ordering option

# **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C Unless otherwise specified)

| Symbol                 | Parameter   | Value                | Units |
|------------------------|---|----------------------|-------|
| T <sub>STG</sub>       | Storage Temperature                                     | -40 to +125          | °C    |
| T <sub>OPR</sub>       | Operating Temperature                                   | -40 to +100          | °C    |
| T <sub>J</sub>         | Junction Temperature                                    | -40 to +125          | °C    |
| T <sub>SOL</sub>       | Lead Solder Temperature                                 | 260 for 10 sec.      | °C    |
| I <sub>F(AVG)</sub>    | Average Input Current <sup>(1)</sup>                    | 25                   | mA    |
| I <sub>F(tr, tf)</sub> | LED Current Minimum Rate of Rise/Fall                   | 250                  | ns    |
| I <sub>F(TRAN)</sub>   | Peak Transient Input Current (<1µs pulse width, 300pps) | 1.0                  | Α     |
| $V_{R}$                | Reverse Input Voltage                                   | 5                    | V     |
| I <sub>OH(PEAK)</sub>  | "High" Peak Output Current <sup>(2)</sup>               | 2.5                  | Α     |
| I <sub>OL(PEAK)</sub>  | "Low" Peak Output Current <sup>(2)</sup>                | 2.5                  | Α     |
| $V_{CC} - V_{EE}$      | Supply Voltage  | -0.5 to 25           | V     |
| V <sub>O(PEAK)</sub>   | Output Voltage  | 0 to V <sub>CC</sub> | V     |
| P <sub>O</sub>         | Output Power Dissipation <sup>(4)</sup>                 | 250                  | mW    |
| $P_{D}$                | Total Power Dissipation <sup>(5)</sup>                  | 295                  | mW    |

# **Recommended Operating Conditions**

| Symbol                            | Parameter           | Value       | Units |
|-----------------------------------|---------------------|-------------|-------|
| V <sub>CC</sub> – V <sub>EE</sub> | Power Supply        | 10 to 20    | V     |
| I <sub>F(ON)</sub>                | Input Current (ON)  | 10 to 16    | mA    |
| V <sub>F(OFF)</sub>               | Input Voltage (OFF) | -3.0 to 0.8 | V     |

# **Electrical-Optical Characteristics (DC)**

Over recommended operating conditions unless otherwise specified.

| Symbol               | Parameter                                   | Test Conditions                               | Min.                 | Тур.* | Max.                  | Unit  |
|----------------------|---|---|----------------------|-------|-----------------------|-------|
| I <sub>OH</sub>      | High Level Output Current <sup>(2)(3)</sup> | $V_{OH} = (V_{CC} - V_{EE} - 1V)$             | 0.5                  |       |                       | Α     |
|                      |   | $V_{OH} = (V_{CC} - V_{EE} - 3V)$             | 2.0                  |       |                       |       |
| I <sub>OL</sub>      | Low Level Output Current <sup>(2)(3)</sup>  | $V_{OL} = (V_{CC} - V_{EE} - 1V)$             | 0.5                  |       |                       | Α     |
|                      |   | $V_{OL} = (V_{CC} - V_{EE} - 3V)$             | 2.0                  |       |                       |       |
| V <sub>OH</sub>      | High Level Output Voltage <sup>(6)(7)</sup> | I <sub>O</sub> = -100mA                       | V <sub>CC</sub> -0.5 |       |                       | V     |
| V <sub>OL</sub>      | Low Level Output Voltage <sup>(6)(7)</sup>  | I <sub>O</sub> = 100mA                        |                      |       | V <sub>EE</sub> + 0.5 | V     |
| I <sub>CCH</sub>     | High Level Supply Current                   | Output Open,<br>I <sub>F</sub> = 10 to 16mA   |                      | 4.8   | 6.0                   | mA    |
| I <sub>CCL</sub>     | Low Level Supply Current                    | Output Open,<br>V <sub>F</sub> = -3.0 to 0.8V |                      | 5.0   | 6.0                   | mA    |
| I <sub>FLH</sub>     | Threshold Input Current Low to High         | $I_O = 0$ mA, $V_O > 5$ V                     |                      |       | 8.0                   | mA    |
| V <sub>FHL</sub>     | Threshold Input Voltage High to Low         | I <sub>O</sub> = 0mA, V <sub>O</sub> < 5V     | 0.8                  |       |                       | V     |
| V <sub>F</sub>       | Input Forward Voltage                       | I <sub>F</sub> = 10mA                         | 1.2                  | 1.43  | 1.8                   | V     |
| $\Delta V_F/T_A$     | Temperature Coefficient of Forward Voltage  | I <sub>F</sub> = 10mA                         |                      | -1.5  |                       | mV/°C |
| V <sub>UVLO+</sub>   | UVLO Threshold                              | $V_{O} > 5V, I_{F} = 10mA$                    |                      | 8.3   |                       | V     |
| V <sub>UVLO</sub>    |   | V <sub>O</sub> < 5V, I <sub>F</sub> = 10mA    |                      | 7.7   |                       | V     |
| UVLO <sub>HYST</sub> | UVLO Hysteresis                             |   |                      | 0.6   |                       | V     |
| BV <sub>R</sub>      | Input Reverse Breakdown Voltage             | I <sub>R</sub> = 10μA                         | 5                    |       |                       | V     |
| C <sub>IN</sub>      | Input Capacitance                           | $f = 1MHz, V_F = 0V$                          |                      | 60    |                       | pF    |

<sup>\*</sup>Typical values at  $T_A = 25$ °C

# **Switching Characteristics**

Over recommended operating conditions unless otherwise specified.

| Symbol   | Parameter   | Test Conditions   | Min. | Тур.* | Max. | Unit  |
|--|---|---|------|-------|------|-------|
| t <sub>PLH</sub>                                       | Propagation Delay Time to High Output Level <sup>(8)</sup>            | I <sub>F</sub> = 10mA,  | 50   | 135   | 200  | ns    |
| t <sub>PHL</sub>                                       | Propagation Delay Time to Low Output Level <sup>(8)</sup>             | $R_g = 10\Omega$ ,<br>f = 250kHz,   | 50   | 105   | 200  | ns    |
| P <sub>WD</sub>  | Pulse Width Distortion <sup>(9)</sup>                                 | Duty Cycle = 50%,   |      |       | 65   | ns    |
| P <sub>DD</sub> (t <sub>PHL</sub> – t <sub>PLH</sub> ) | Propagation Delay Difference Between Any<br>Two Parts <sup>(10)</sup> | C <sub>g</sub> = 10nF   | -90  |       | 90   | ns    |
| t <sub>r</sub>   | Rise Time   | C <sub>L</sub> = 10nF,  |      | 75    |      | ns    |
| t <sub>f</sub>   | Fall Time   | $R_g = 10\Omega$  |      | 55    |      | ns    |
| t <sub>UVLO ON</sub>                                   | UVLO Turn On Delay  |   |      | 2.0   |      | μs    |
| t <sub>UVLO OFF</sub>                                  | UVLO Turn Off Delay   |   |      | 0.3   |      | μs    |
| I CM <sub>H</sub> I                                    | Output High Level Common Mode Transient Immunity <sup>(11)</sup> (12) | $T_A = +25$ °C,<br>$I_f = 10 \text{ to } 16\text{mA},$<br>$V_{CM} = 1.5\text{kV},$<br>$V_{CC} = 20\text{V}$ | 10   |       |      | kV/µs |
| I CM <sub>L</sub> I                                    | Output Low Level Common Mode Transient Immunity <sup>(11)</sup> (13)  | $T_{A} = +25^{\circ}\text{C},$ $V_{f} = 0\text{V},$ $V_{CM} = 1.5\text{kV},$ $V_{CC} = 20\text{V}$          | 10   |       |      | kV/μs |

<sup>\*</sup>Typical values at  $T_A = 25^{\circ}C$ 

# **Isolation Characteristics**

| Symbol           | Parameter  | Test Conditions  | Min. | Тур.*            | Max. | Unit             |
|------------------|--|--|------|------------------|------|------------------|
| V <sub>ISO</sub> | Withstand Isolation Voltage <sup>(14) (15)</sup> | $T_A = 25^{\circ}C$ ,<br>R.H. < 50%, t = 1min.,<br>$I_{I-O} \le 20\mu A$ | 5000 |                  |      | V <sub>rms</sub> |
| R <sub>I-O</sub> | Resistance (input to output) <sup>(15)</sup>     | V <sub>I-O</sub> = 500V  |      | 10 <sup>11</sup> |      | Ω                |
| C <sub>I-O</sub> | Capacitance (input to output)                    | Freq. = 1MHz   |      | 1                |      | pF               |

<sup>\*</sup>Typical values at  $T_A = 25$ °C

#### Notes:

- 1. Derate linearly above +70°C free air temperature at a rate of 0.3mA/°C.
- 2. The output currents  $I_{OH}$  and  $I_{OL}$  are specified with a capacitive current limited load =  $(3 \times 0.01 \mu F) + 0.5 \Omega$ , frequency = 8kHz, 50% DF. The maximum pulse width of the output current is 300ns, maximum duty cycle = 0.48%. Output currents specified for different values of  $V_{DS}$  for  $V_{CC} V_{EE} = 20V$  with the formula:

$$V_{OH} = (V_{CC} - V_{EE}) - (I_{OH} \times R_{DS(ON)}).$$

This guarantees operation at I<sub>O</sub> peak minimum = 2.0A for -40°C to +100°C operating temperature range.

3. The output currents  $I_{OH}$  and  $I_{OL}$  are specified with a capacitive current limited load =  $(3 \times 0.01 \mu F) + 8.5 \Omega$ , frequency = 8kHz, 50% DF. The maximum pulse width of the output current is 1.5 $\mu$ s, maximum duty cycle = 2.4%. Output currents specified for different values of  $V_{DS}$  for  $V_{CC} - V_{EE} = 20V$  with the formula:

$$V_{OL} = (V_{CC} - V_{EE}) - (I_{OL} \times R_{DS(ON)}).$$

This guarantees operation at  $I_O$  peak minimum = 0.5A for -40°C to +100°C operating temperature range.

- 4. Derate linearly above +87°C, free air temperature at the rate of 0.77mW/°C. Refer to Figure 12.
- 5. No derating required across operating temperature range.
- 6. In this test, V<sub>OH</sub> is measured with a dc load current. When driving capacitive load V<sub>OH</sub> will approach V<sub>CC</sub> as I<sub>OH</sub> approaches zero amps.
- 7. Maximum pulse width = 1ms, maximum duty cycle = 20%.
- 8.  $t_{PHL}$  propagation delay is measured from the 50% level on the falling edge of the input pulse to the 50% level of the falling edge of the  $V_O$  signal.  $t_{PLH}$  propagation delay is measured from the 50% level on the rising edge of the input pulse to the 50% level of the rising edge of the  $V_O$  signal.
- 9. PWD is defined as I t<sub>PHL</sub> t<sub>PLH</sub> I for any given device.
- 10. The difference between  $t_{PHL}$  and  $t_{PLH}$  between any two FOD3180 parts under same test conditions.
- 11. Pin 1 and 4 need to be connected to LED common.
- 12. Common mode transient immunity in the high state is the maximum tolerable  $dV_{CM}/dt$  of the common mode pulse  $V_{CM}$  to assure that the output will remain in the high state (i.e.  $V_O > 10.0V$ ).
- 13. Common mode transient immunity in a low state is the maximum tolerable  $dV_{CM}/dt$  of the common mode pulse,  $V_{CM}$ , to assure that the output will remain in a low state (i.e.  $V_O < 1.0V$ ).
- 14. In accordance with UL 1577, each optocoupler is proof tested by applying an insulation test voltage > 6000Vrms for 1 second (leakage detection current limit  $I_{I-O}$  <  $5\mu A$ ).

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15. Device considered a two-terminal device: pins on input side shorted together and pins on output side shorted together.

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# **Typical Performance Curves**

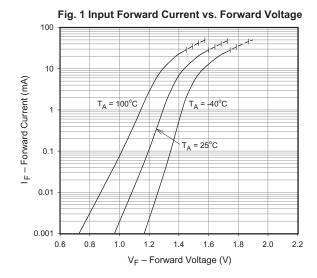


Fig. 2 Low To High Input Current Threshold vs. Ambient Temperature

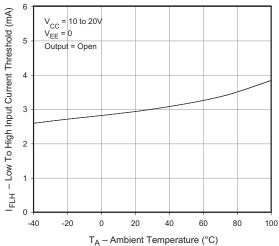


Fig. 3 Output Low Voltage vs. Ambient Temperature

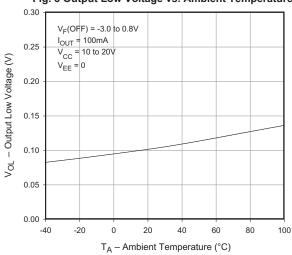


Fig. 4 High Output Voltage Drop vs. Ambient Temperature

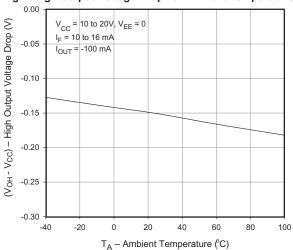


Fig. 5 Supply Current vs. Ambient Temperature

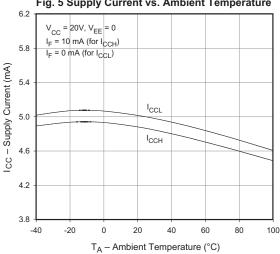
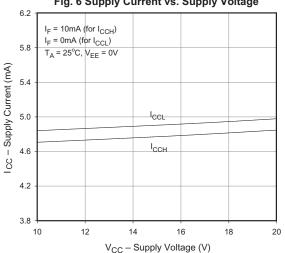
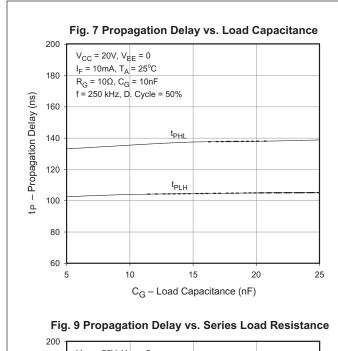
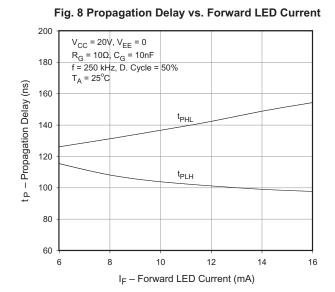


Fig. 6 Supply Current vs. Supply Voltage



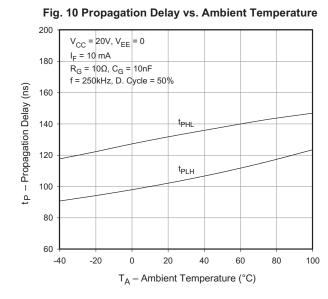


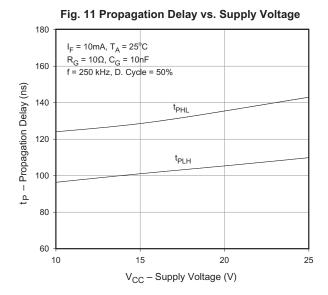


 $V_{CC} = 20V, V_{EE} = 0$   $I_{F} = 10\text{mA}, T_{A} = 25^{\circ}\text{C}$   $C_{G} = 10\text{nF}$  f = 250 kHz, D. Cycle = 50% 140  $U_{CC} = 10\text{nF}$   $U_{CC} = 10\text{nF}$ 

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R<sub>G</sub> – Series Load Resistance (Ω)





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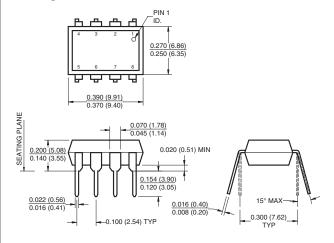
80

60

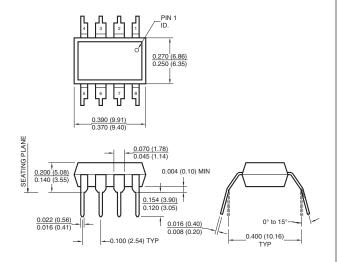
10

# **Package Dimensions**

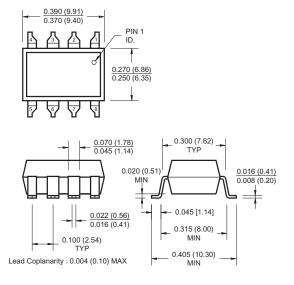
## **Through Hole**



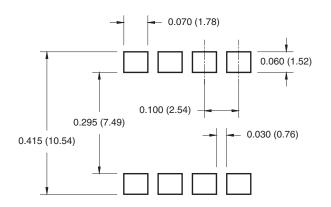
## 0.4" Lead Spacing



### **Surface Mount**



## 8-Pin DIP - Land Pattern



## Note:

All dimensions are in inches (millimeters)

# **Ordering Information**

Example: FOD3180 X

## X Packaging Option

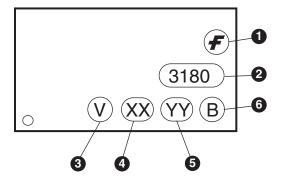
S: Surface Mount Lead Bend SD: Surface Mount, Tape and Reel

T: 0.4" Lead Spacing V: VDE Approved

TV: VDE Approved, 0.4" Lead Spacing SV: VDE Approved, Surface Mount

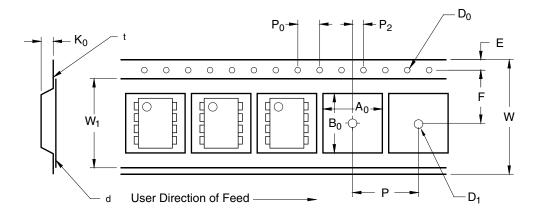
SDV: VDE Approved, Surface Mount, Tape and Reel

# **Marking Information**



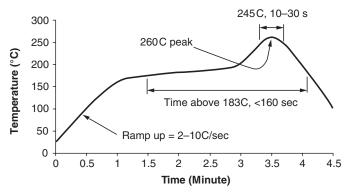
| Definitions |  |  |  |  |
|-------------|--|--|--|--|
| 1           | Fairchild logo   |  |  |  |
| 2           | Device number  |  |  |  |
| 3           | VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table) |  |  |  |
| 4           | Two digit year code, e.g., '03'  |  |  |  |
| 5           | Two digit work week ranging from '01' to '53'  |  |  |  |
| 6           | Assembly package code  |  |  |  |

# **Carrier Tape Specifications**



| Symbol         | Description                     | Dimension in mm |
|----------------|---------------------------------|-----------------|
| W              | Tape Width                      | 16.0 ± 0.3      |
| t              | Tape Thickness                  | 0.30 ± 0.05     |
| P <sub>0</sub> | Sprocket Hole Pitch             | 4.0 ± 0.1       |
| D <sub>0</sub> | Sprocket Hole Diameter          | 1.55 ± 0.05     |
| E              | Sprocket Hole Location          | 1.75 ± 0.10     |
| F              | Pocket Location                 | 7.5 ± 0.1       |
| P <sub>2</sub> |                                 | 4.0 ± 0.1       |
| Р              | Pocket Pitch                    | 12.0 ± 0.1      |
| A <sub>0</sub> | Pocket Dimensions               | 10.30 ±0.20     |
| B <sub>0</sub> |                                 | 10.30 ±0.20     |
| K <sub>0</sub> |                                 | 4.90 ±0.20      |
| W <sub>1</sub> | Cover Tape Width                | 1.6 ± 0.1       |
| d              | Cover Tape Thickness            | 0.1 max         |
|                | Max. Component Rotation or Tilt | 10°             |
| R              | Min. Bending Radius             | 30              |

## **Reflow Profile**



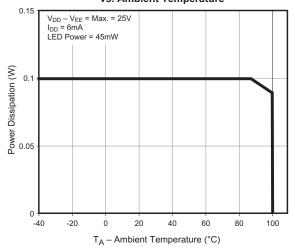
- Peak reflow temperature: 260C (package surface temperature)
- Time of temperature higher than 183C for 160 seconds or less
- · One time soldering reflow is recommended

## **Output Power Derating**

The maximum package power dissipation is 295mW. The package is limited to this level to ensure that under normal operating conditions and over extended temperature range that the semiconductor junction temperatures do not exceed 125°C. The package power is composed of three elements; the LED, static operating power of the output IC, and the power dissipated in the output power MOSFET transistors. The power rating of the output IC is 250mW. This power is divided between the static power of the integrated circuit, which is the product of  $I_{DD}$  times the power supply voltage  $(V_{DD}-V_{EE})$ . The maximum IC static output power is 150mW,  $(V_{DD}-V_{EE})=25\text{V},\,I_{DD}=6\text{mA}$ . This maximum condition is valid over the operational temperature range of -40°C to +100°C. Under these maximum operating conditions, the output of the power MOSFET is allowed to dissipate 100mW of power.

The absolute maximum output power dissipation versus ambient temperature is shown in Figure 12. The output driver is capable of supplying 100mW of output power over the temperature range from -40°C to 87°C. The output derates to 90mW at the absolute maximum operating temperature of 100°C.

Fig. 12 Absolute Maximum Power Dissipation vs. Ambient Temperature



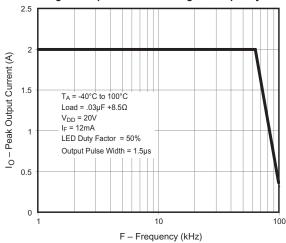
The output power is the product of the average output current squared times the output transistor's  $R_{DS(ON)}$ :

$$P_{O(AVG)} = I_{O(AVG)} 2 \cdot R_{DS(ON)}$$

The  $I_{O(AVG)}$  is the product of the duty factor times the peak current flowing in the output. The duty factor is the ratio of the 'on' time of the output load current divided by the period of the operating frequency. An  $R_{DS(ON)}$  of  $2.0\Omega$  results in an average output load current of 200mA. The load duty factor is a ratio of the average output time of the power MOSFET load circuit and period of the driving frequency.

The maximum permissible, operating frequency is determined by the load supplied to the output at its resulting output pulse width. Figure 13 shows an example of a  $0.03\mu F$  gate to source capacitance with a series resistance of  $8.50\Omega$ . This reactive load results in a composite average pulse width of 1.5 $\mu$ s. Under this load condition it is not necessary to derate the absolute maximum output current until the frequency of operation exceeds 63kHz.

Fig. 13 Output Current Derating vs. Frequency



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# I<sub>OH</sub> and I<sub>OL</sub> Test Conditions

This device is tested and specified when driving a complex reactive load. The load consists of a capacitor in the series with a current limiting resistor. The capacitor represents the gate to source capacitance of a power MOSFET transistor. The test load is a 0.03uF capacitor in series with an  $8.5\Omega$  resistor. The LED test frequency is 10.0kHz with a 50% duty cycle. The combined  $I_{OH}$  and  $I_{OL}$  output load current duty factor is 0.6% at the test frequency.

Figure 14 illustrates the relationship of the LED input drive current and the device's output voltage and sourcing and sinking currents. The  $0.03\mu F$  capacitor load represents the gate to source capacitance of a very large power MOSFET transistor. A single supply voltage of 20V is used in the evaluation.

Figure 15 shows the test schematic to evaluate the output voltage and sourcing and sinking capability of the device. The  $I_{OH}$  and  $I_{OL}$  are measured at the peak of their respective current pulses.

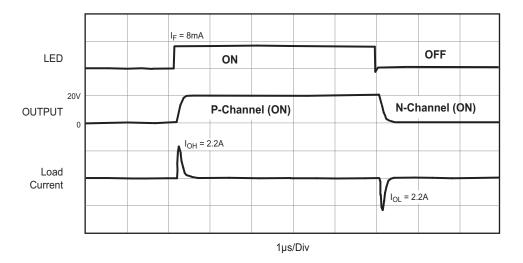


Figure 14. FOD 3180 Output Current and Output Voltage vs. LED Drive

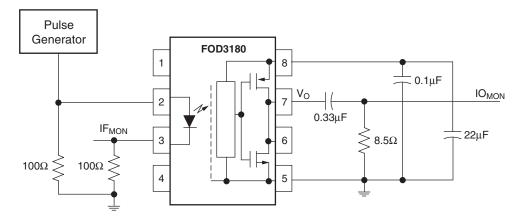


Figure 15. Test Schematic



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FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

#### As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

| Datasheet Identification | Product Status         | Definition   |
|--------------------------|------------------------|--|
| Advance Information      | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.   |
| Preliminary              | First Production       | This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| No Identification Needed | Full Production        | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.   |
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